

TO-92MOD Plastic-Encapsulate Transistors

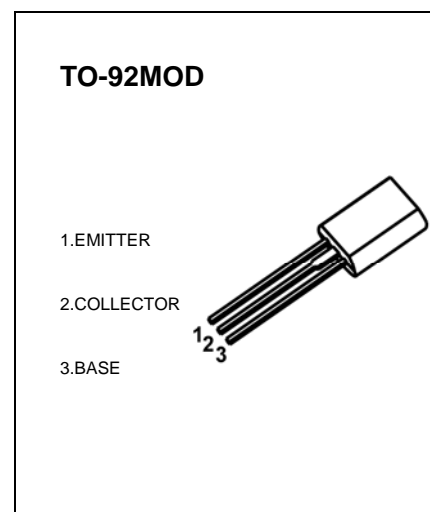
3CG751 TRANSISTOR (PNP)

FEATURE

- High power amplifier
- Low $V_{CE(sat)}$

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.5	A
P_C	Collector Power Dissipation	0.9	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55 to +150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}$, $I_E = 0$	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{ mA}$, $I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}$, $I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -30\text{ V}$, $I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}$, $I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -2\text{ V}$, $I_C = -500\text{ mA}$	100		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1.5\text{ A}$, $I_B = -30\text{ mA}$			-2	V
Transition frequency	f_T	$V_{CE} = -5\text{ V}$, $I_C = -100\text{ mA}$	50			MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$			80	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-240	150-400